

Product Change Notification



Date: FEBRUARY 13, 2015

PCN#: 140A00238

Subject: AC TIMING CHANGES FOR THE 1600Mbs 4GB DDR3 LP devices

Dear Customers,

Microsemi Power and Microelectronics Group wishes to inform you of a change in the AC Timing parameters; t_{DS} , t_{DH} , and t_{DQSK} for the 1600Mbs data rate of the 4GB DDR3 LP devices.

Auto Precharge is required for the READ and WRITES operations of the 1600Mbs data rate devices. The following timing parameters will be changed for the 1600Mbs data rate devices.

- Input data setup timing, t_{DS} will be increased from 160ps to 200ps
- Input data hold timing, t_{DH} will be increased from 145ps to 170ps
- DQ strobe output timing, t_{DQSK} will be updated from -225ps to -245ps

This specification change is required for the 4GB DDR3 LP 1600Mbs devices based on product characterization results.

This change affects the following parts:

[W3J512M72K-1600LBC](#), [W3J512M72K-1600LBI](#), [W3J512M72K-1600LBM](#), [W3J512M72G-1600LBC](#), [W3J512M72G-1600LBI](#), [W3J512M72G-1600LBM](#)

Best regards,

Microsemi Memory and Storage Solutions Engineering